



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Tatsuya Usami

Serial No.: 09/851,313

Group Art Unit: 2823

Filed: May 9, 2001

Examiner: Maldonado, J.

For: SEMICONDUCTOR DEVICE AND SEMICONDUCTOR WAFER

Honorable Commissioner of Patents
Washington, D.C. 20231

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AMENDMENT UNDER 37 C.F.R. §1.116

Sir:

In response to the Office Action dated **November 6, 2002**, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend the following claims:

1. (Amended) A semiconductor device comprising:

a multi-layered insulation film formed on a semiconductor substrate, said multi-

layered insulation film comprising:

a first insulation layer comprising an organic material having a dielectric constant which is lower than a silicon oxide dielectric constant;

a second insulation layer comprising a polysiloxane compound having an Si-H group and formed on and adhering to a top of said first insulation layer;

a third insulation layer comprising an inorganic material and formed on and adhering to a top of said second insulation layer; and

a plurality of wires formed in said multi-layered insulation film, said multi-layered insulation film being disposed between said wires.

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